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<b>INFORMATION DISCLOSURE STATEMENT TRANSMITTAL</b>  To Commissioner For Patents Enclosed herewith is a Form PTO-1449, any required copies of documents listed thereon, and any concise explanation of their relevance is indicated below per 37 CFR 1.97.	<b>Application Number</b>	
	<b>Filing Date</b>	
	<b>First Named Inventor</b>	SHANNON, JOHN M.
	<b>Group Art Unit</b>	
	<b>Examiner Name</b>	
	<b>Atty. Docket Number</b>	GB04 0023 US1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number No.-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS						
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NON-PATENT LITERATURE DOCUMENTS						
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	1	GADELRAH S. M. : "THE SOURCE-GATED AMORPHOUS SILICON PHOTO-TRANSISTOR"; IEEE ELECTRON DEVICES VOL. 44 NO. 10; OCT. 1997. PP 1789-1794.				
	2	SHANNON J. M. ET AL. : "SOURCE-GATED THIN-FILM TRANSISTORS"; IEEE ELECTRON DEVICE LETTERS VOL. 24 NO. 6; JUNE 2003. PP 405-407.				

<b>Examiner Signature</b>		<b>Date Considered</b>	
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